



BGA2815

MMIC wideband amplifier

Rev. 5 — 29 May 2015

Product data sheet

1. Product profile

1.1 General description

Silicon Monolithic Microwave Integrated Circuit (MMIC) wideband amplifier with internal matching circuit in a 6-pin SOT363 plastic SMD package.

1.2 Features and benefits

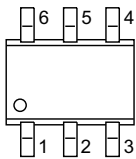
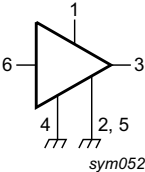
- Input internally matched to $50\ \Omega$
- A gain of 25.8 dB at 250 MHz decreasing to 24.7 dB at 2150 MHz
- Output power at 1 dB gain compression = 6 dBm
- Supply current = 18.2 mA at a supply voltage of 3.3 V
- Reverse isolation > 38 dB up to 2 GHz
- Good linearity with low second order and third order products
- Noise figure = 3.8 dB at 950 MHz
- Unconditionally stable ($K > 1$)
- No output inductor required

1.3 Applications

- LNB IF amplifiers
- General purpose low noise wideband amplifier for frequencies between DC and 2.2 GHz

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	V_{CC}		 sym052
2, 5	GND2		
3	RF_OUT		
4	GND1		
6	RF_IN		



3. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BGA2815	-	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 3. Marking

Type number	Marking code	Description
BGA2815	*E9	* = - : made in Hong Kong
		* = p : made in Hong Kong
		* = W : made in China
		* = t : made in Malaysia

5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage	RF input AC coupled	-0.5	+5.0	V
I_{CC}	supply current		-	55	mA
P_{tot}	total power dissipation	$T_{sp} = 90\text{ °C}$	-	200	mW
T_{stg}	storage temperature		-40	+125	°C
T_j	junction temperature		-	125	°C
P_{drive}	drive power		-	10	dBm

6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	$P_{tot} = 200\text{ mW}$; $T_{sp} = 90\text{ °C}$	300	K/W

7. Characteristics

Table 6. Characteristics

$V_{CC} = 3.3\text{ V}$; $Z_S = Z_L = 50\ \Omega$; $P_i = -40\text{ dBm}$; $T_{amb} = 25\text{ °C}$; measured on demo board; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		3.0	3.3	3.6	V
I_{CC}	supply current		15.7	18.2	21.1	mA

Table 6. Characteristics ...continued

$V_{CC} = 3.3\text{ V}$; $Z_S = Z_L = 50\ \Omega$; $P_i = -40\text{ dBm}$; $T_{amb} = 25\text{ }^\circ\text{C}$; measured on demo board; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G _p	power gain	f = 250 MHz	25.2	25.8	26.4	dB
		f = 950 MHz	24.6	25.3	26.0	dB
		f = 2150 MHz	23.2	24.7	26.2	dB
RL _{in}	input return loss	f = 250 MHz	11	13	15	dB
		f = 950 MHz	11	13	15	dB
		f = 2150 MHz	11	14	20	dB
RL _{out}	output return loss	f = 250 MHz	14	18	23	dB
		f = 950 MHz	15	16	17	dB
		f = 2150 MHz	17	19	22	dB
ISL	isolation	f = 250 MHz	40	55	76	dB
		f = 950 MHz	43	45	46	dB
		f = 2150 MHz	36	38	41	dB
NF	noise figure	f = 250 MHz	3.2	3.7	4.2	dB
		f = 950 MHz	3.4	3.8	4.3	dB
		f = 2150 MHz	3.2	3.7	4.1	dB
B _{-3dB}	-3 dB bandwidth	3 dB below gain at 1 GHz	2.8	3.0	3.1	GHz
K	Rollett stability factor	f = 250 MHz	10	14	20	
		f = 950 MHz	3.5	4.5	6.5	
		f = 2150 MHz	1.5	2	2.5	
P _{L(sat)}	saturated output power	f = 250 MHz	7	8	8	dBm
		f = 950 MHz	3	5	6	dBm
		f = 2150 MHz	-1	+1	+2	dBm
P _{L(1dB)}	output power at 1 dB gain compression	f = 250 MHz	6	6	7	dBm
		f = 950 MHz	3	5	6	dBm
		f = 2150 MHz	-1	+1	+2	dBm
IP3 _I	input third-order intercept point	P _{drive} = -38 dBm (for each tone)				
		f ₁ = 250 MHz; f ₂ = 251 MHz	-8	-6	-4	dBm
		f ₁ = 950 MHz; f ₂ = 951 MHz	-11	-8	-6	dBm
		f ₁ = 2150 MHz; f ₂ = 2151 MHz	-18	-15	-12	dBm
IP3 _O	output third-order intercept point	P _{drive} = -38 dBm (for each tone)				
		f ₁ = 250 MHz; f ₂ = 251 MHz	18	20	22	dBm
		f ₁ = 950 MHz; f ₂ = 951 MHz	15.5	17.5	19.5	dBm
		f ₁ = 2150 MHz; f ₂ = 2151 MHz	7.5	10.5	13.5	dBm
P _{L(2H)}	second harmonic output power	P _{drive} = -35 dBm				
		f _{1H} = 250 MHz; f _{2H} = 500 MHz	-54	-52	-50	dBm
		f _{1H} = 950 MHz; f _{2H} = 1900 MHz	-46	-44	-43	dBm
ΔIM2	second-order intermodulation distance	P _{drive} = -38 dBm (for each tone)				
		f ₁ = 250 MHz; f ₂ = 251 MHz	42	53	64	dBc
		f ₁ = 950 MHz; f ₂ = 951 MHz	39	51	62	dBc

8. Application information

Figure 1 shows a typical application circuit for the BGA2815 MMIC. The device is internally matched to 50 Ω and therefore does not need any external matching. The value of the input and output DC blocking capacitors C2 and C3 should not be more than 100 pF for applications above 100 MHz. However, when the device is operated below 100 MHz, the capacitor value should be increased.

The location of the 470 pF supply decoupling capacitor (C_{dec}) can be precisely chosen for optimum performance.

The PCB top ground plane, connected to pins 2, 4 and 5 must be as close as possible to the MMIC, preferably also below the MMIC. When using via holes, use multiple via holes as close as possible to the MMIC.

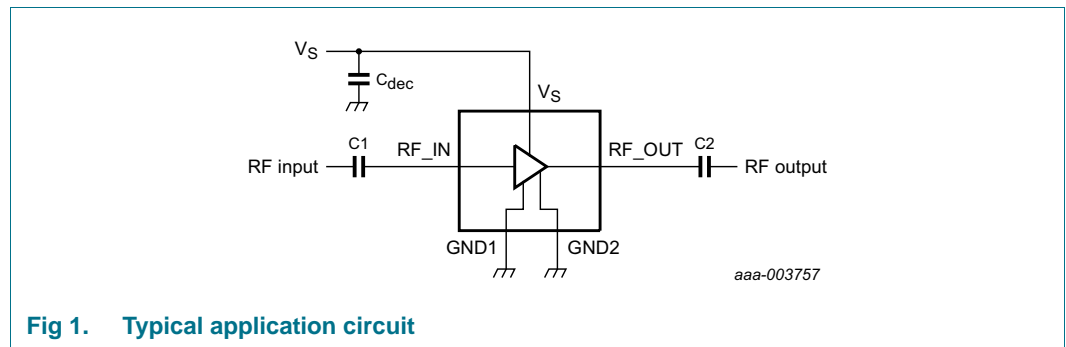
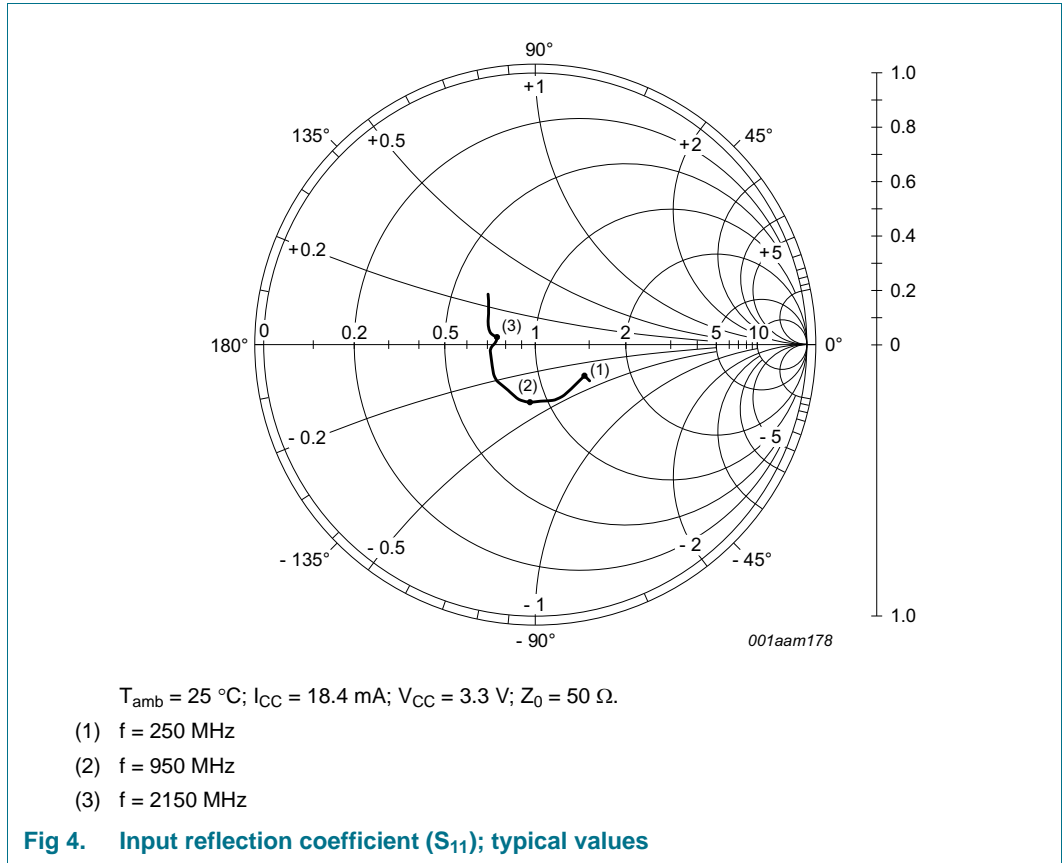


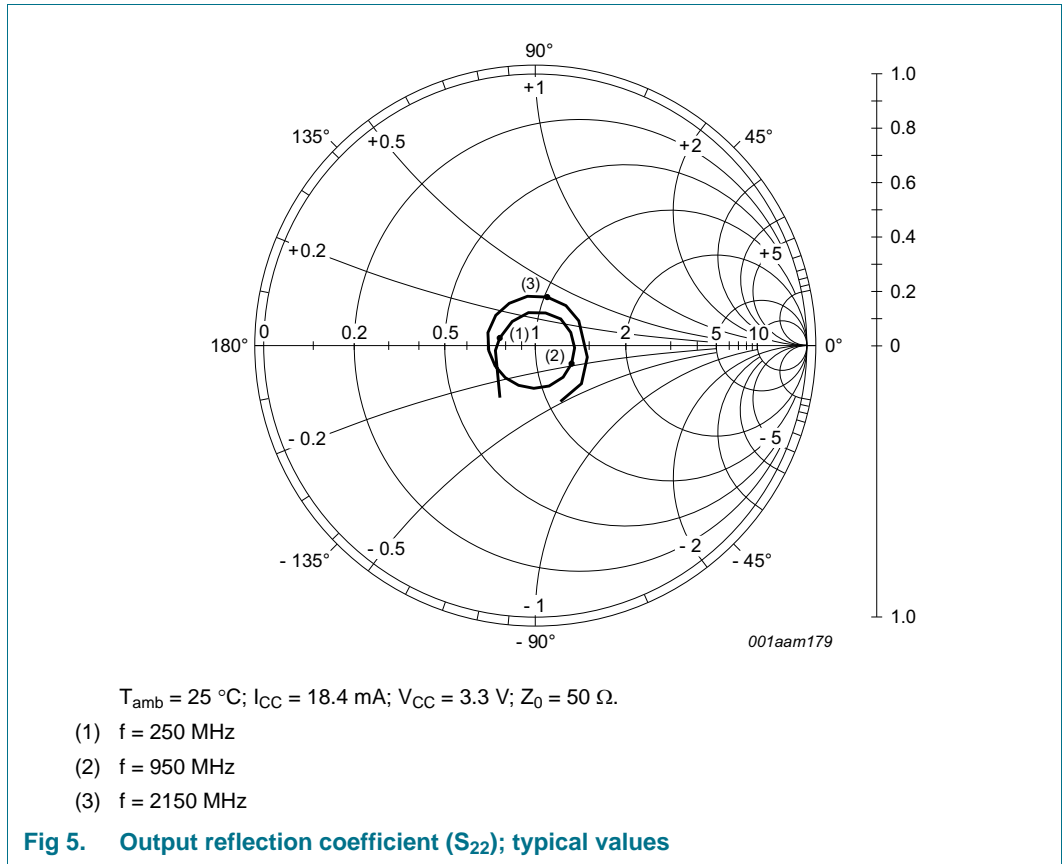
Fig 1. Typical application circuit

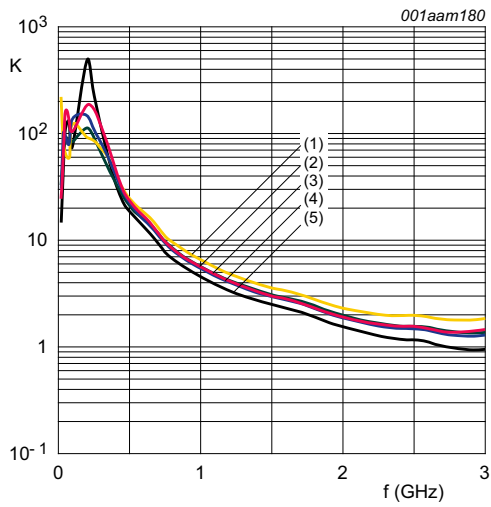
8.1 Application examples

<p>The MMIC is very suitable as IF amplifier in e.g. LNB's. The excellent wideband characteristics make it an easy building block.</p>	<p>As second amplifier after an LNA, the MMIC offers an easy matching, low noise solution.</p>
Fig 2. Application as IF amplifier	Fig 3. Application as RF amplifier

8.2 Graphs



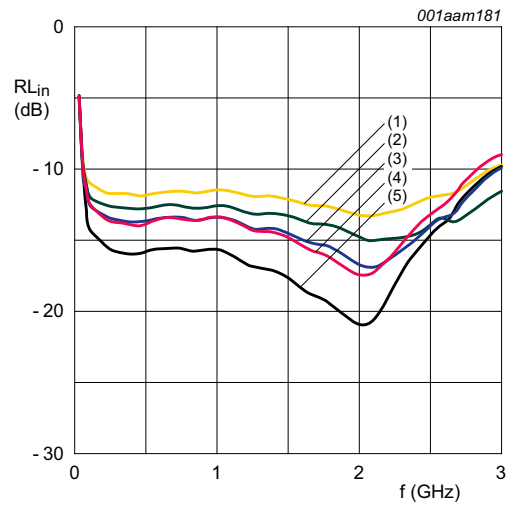




$P_{drive} = -40 \text{ dBm}; Z_0 = 50 \Omega.$

- (1) $V_{CC} = 3.0 \text{ V}; T_{amb} = 85 \text{ }^\circ\text{C}; I_{CC} = 15.93 \text{ mA}.$
- (2) $V_{CC} = 3.0 \text{ V}; T_{amb} = -40 \text{ }^\circ\text{C}; I_{CC} = 16.12 \text{ mA}.$
- (3) $V_{CC} = 3.3 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}; I_{CC} = 18.41 \text{ mA}.$
- (4) $V_{CC} = 3.6 \text{ V}; T_{amb} = 85 \text{ }^\circ\text{C}; I_{CC} = 20.11 \text{ mA}.$
- (5) $V_{CC} = 3.6 \text{ V}; T_{amb} = -40 \text{ }^\circ\text{C}; I_{CC} = 20.23 \text{ mA}.$

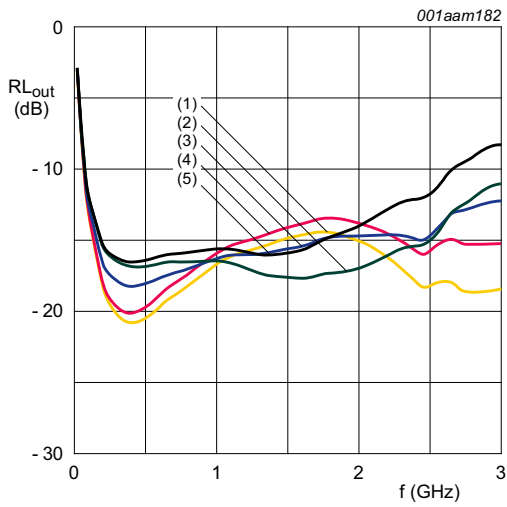
Fig 6. Rollett stability factor as function of frequency; typical values



$P_{drive} = -40 \text{ dBm}; Z_0 = 50 \Omega.$

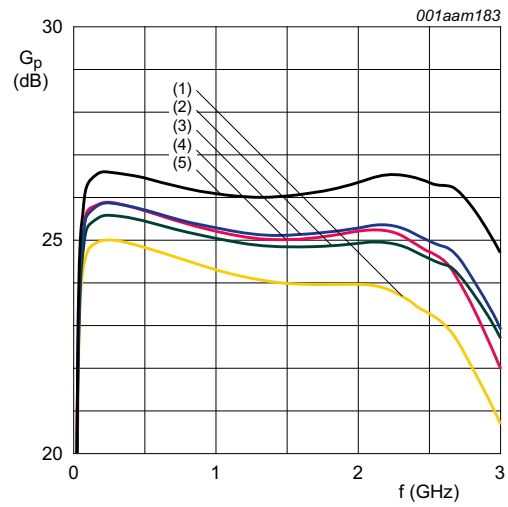
- (1) $V_{CC} = 3.0 \text{ V}; T_{amb} = 85 \text{ }^\circ\text{C}; I_{CC} = 15.93 \text{ mA}.$
- (2) $V_{CC} = 3.0 \text{ V}; T_{amb} = -40 \text{ }^\circ\text{C}; I_{CC} = 16.12 \text{ mA}.$
- (3) $V_{CC} = 3.3 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}; I_{CC} = 18.41 \text{ mA}.$
- (4) $V_{CC} = 3.6 \text{ V}; T_{amb} = 85 \text{ }^\circ\text{C}; I_{CC} = 20.11 \text{ mA}.$
- (5) $V_{CC} = 3.6 \text{ V}; T_{amb} = -40 \text{ }^\circ\text{C}; I_{CC} = 20.23 \text{ mA}.$

Fig 7. Input return loss as function of frequency; typical values



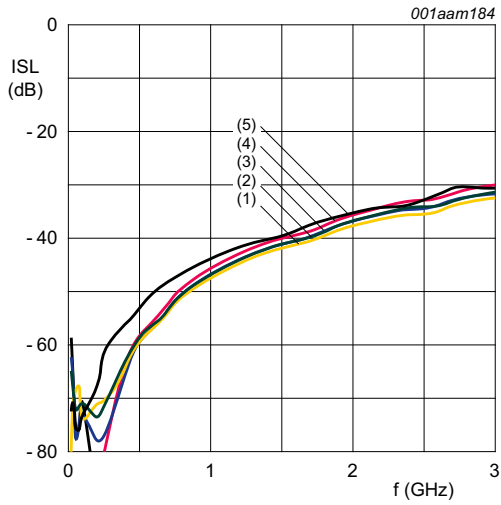
- $P_{drive} = -40 \text{ dBm}; Z_0 = 50 \Omega.$
- (1) $V_{CC} = 3.0 \text{ V}; T_{amb} = 85 \text{ }^\circ\text{C}; I_{CC} = 15.93 \text{ mA}.$
 - (2) $V_{CC} = 3.0 \text{ V}; T_{amb} = -40 \text{ }^\circ\text{C}; I_{CC} = 16.12 \text{ mA}.$
 - (3) $V_{CC} = 3.3 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}; I_{CC} = 18.41 \text{ mA}.$
 - (4) $V_{CC} = 3.6 \text{ V}; T_{amb} = 85 \text{ }^\circ\text{C}; I_{CC} = 20.11 \text{ mA}.$
 - (5) $V_{CC} = 3.6 \text{ V}; T_{amb} = -40 \text{ }^\circ\text{C}; I_{CC} = 20.23 \text{ mA}.$

Fig 8. Output return loss as function of frequency; typical values



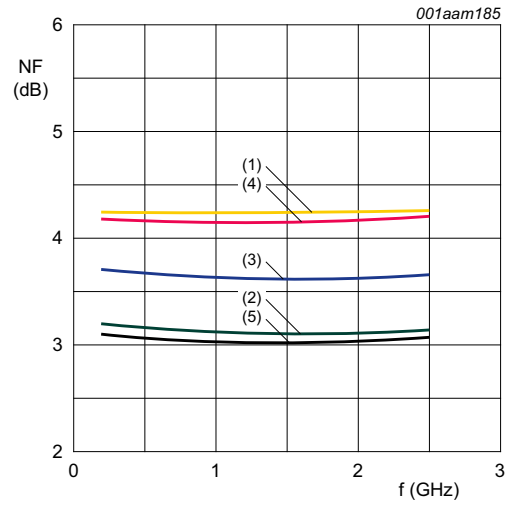
- $P_{drive} = -40 \text{ dBm}; Z_0 = 50 \Omega.$
- (1) $V_{CC} = 3.0 \text{ V}; T_{amb} = 85 \text{ }^\circ\text{C}; I_{CC} = 15.93 \text{ mA}.$
 - (2) $V_{CC} = 3.0 \text{ V}; T_{amb} = -40 \text{ }^\circ\text{C}; I_{CC} = 16.12 \text{ mA}.$
 - (3) $V_{CC} = 3.3 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}; I_{CC} = 18.41 \text{ mA}.$
 - (4) $V_{CC} = 3.6 \text{ V}; T_{amb} = 85 \text{ }^\circ\text{C}; I_{CC} = 20.11 \text{ mA}.$
 - (5) $V_{CC} = 3.6 \text{ V}; T_{amb} = -40 \text{ }^\circ\text{C}; I_{CC} = 20.23 \text{ mA}.$

Fig 9. Power gain as function of frequency; typical values



$P_{drive} = -40 \text{ dBm}; Z_0 = 50 \Omega.$
 (1) $V_{CC} = 3.0 \text{ V}; T_{amb} = 85 \text{ }^\circ\text{C}; I_{CC} = 15.93 \text{ mA}.$
 (2) $V_{CC} = 3.0 \text{ V}; T_{amb} = -40 \text{ }^\circ\text{C}; I_{CC} = 16.12 \text{ mA}.$
 (3) $V_{CC} = 3.3 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}; I_{CC} = 18.41 \text{ mA}.$
 (4) $V_{CC} = 3.6 \text{ V}; T_{amb} = 85 \text{ }^\circ\text{C}; I_{CC} = 20.11 \text{ mA}.$
 (5) $V_{CC} = 3.6 \text{ V}; T_{amb} = -40 \text{ }^\circ\text{C}; I_{CC} = 20.23 \text{ mA}.$

Fig 10. Isolation as function of frequency; typical values



$Z_0 = 50 \Omega.$
 (1) $V_{CC} = 3.0 \text{ V}; T_{amb} = 85 \text{ }^\circ\text{C}; I_{CC} = 15.93 \text{ mA}.$
 (2) $V_{CC} = 3.0 \text{ V}; T_{amb} = -40 \text{ }^\circ\text{C}; I_{CC} = 16.12 \text{ mA}.$
 (3) $V_{CC} = 3.3 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}; I_{CC} = 18.41 \text{ mA}.$
 (4) $V_{CC} = 3.6 \text{ V}; T_{amb} = 85 \text{ }^\circ\text{C}; I_{CC} = 20.11 \text{ mA}.$
 (5) $V_{CC} = 3.6 \text{ V}; T_{amb} = -40 \text{ }^\circ\text{C}; I_{CC} = 20.23 \text{ mA}.$

Fig 11. Noise figure as function of frequency; typical values

8.3 Tables

Table 7. Supply current over temperature and supply voltages
Typical values.

Symbol	Parameter	Conditions	$T_{amb} \text{ (}^\circ\text{C)}$			Unit
			-40	+25	+85	
I_{CC}	supply current	$V_{CC} = 3.0 \text{ V}$	16.12	16.34	15.93	mA
		$V_{CC} = 3.3 \text{ V}$	18.76	18.41	17.95	mA
		$V_{CC} = 3.6 \text{ V}$	20.23	19.91	20.11	mA

Table 8. Second harmonic output power over temperature and supply voltages
Typical values.

Symbol	Parameter	Conditions	$T_{amb} \text{ (}^\circ\text{C)}$			Unit	
			-40	+25	+85		
$P_{L(2H)}$	second harmonic output power	$f = 250 \text{ MHz}; P_{drive} = -35 \text{ dBm}$	$V_{CC} = 3.0 \text{ V}$	-49	-51	-53	dBm
			$V_{CC} = 3.3 \text{ V}$	-51	-53	-54	dBm
			$V_{CC} = 3.6 \text{ V}$	-52	-54	-55	dBm
		$f = 950 \text{ MHz}; P_{drive} = -35 \text{ dBm}$	$V_{CC} = 3.0 \text{ V}$	-43	-44	-45	dBm
			$V_{CC} = 3.3 \text{ V}$	-43	-44	-45	dBm
			$V_{CC} = 3.6 \text{ V}$	-43	-44	-45	dBm

Table 9. Input power at 1 dB gain compression over temperature and supply voltages
Typical values.

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
P _{i(1dB)}	input power at 1 dB gain compression	f = 250 MHz				
		V _{CC} = 3.0 V	-19	-19	-19	dBm
		V _{CC} = 3.3 V	-18	-18	-19	dBm
		V _{CC} = 3.6 V	-18	-18	-18	dBm
		f = 950 MHz				
		V _{CC} = 3.0 V	-19	-20	-20	dBm
		V _{CC} = 3.3 V	-19	-19	-20	dBm
		V _{CC} = 3.6 V	-19	-19	-20	dBm
		f = 2150 MHz				
		V _{CC} = 3.0 V	-22	-23	-24	dBm
		V _{CC} = 3.3 V	-23	-23	-24	dBm
		V _{CC} = 3.6 V	-23	-23	-24	dBm

Table 10. Output power at 1 dB gain compression over temperature and supply voltages
Typical values.

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
P _{L(1dB)}	output power at 1 dB gain compression	f = 250 MHz				
		V _{CC} = 3.0 V	6	6	5	dBm
		V _{CC} = 3.3 V	7	7	6	dBm
		V _{CC} = 3.6 V	8	7	6	dBm
		f = 950 MHz				
		V _{CC} = 3.0 V	5	4	3	dBm
		V _{CC} = 3.3 V	5	5	4	dBm
		V _{CC} = 3.6 V	6	5	4	dBm
		f = 2150 MHz				
		V _{CC} = 3.0 V	+2	0	-2	dBm
		V _{CC} = 3.3 V	+2	+1	-1	dBm
		V _{CC} = 3.6 V	3	1	0	dBm

Table 11. Saturated output power over temperature and supply voltages*Typical values.*

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
P _{L(sat)}	saturated output power	f = 250 MHz				
		V _{CC} = 3.0 V	7	7	7	dBm
		V _{CC} = 3.3 V	8	8	7	dBm
		V _{CC} = 3.6 V	9	9	8	dBm
		f = 950 MHz				
		V _{CC} = 3.0 V	5	4	3	dBm
		V _{CC} = 3.3 V	5	5	4	dBm
		V _{CC} = 3.6 V	6	5	4	dBm
		f = 2150 MHz				
		V _{CC} = 3.0 V	+2	+1	-1	dBm
		V _{CC} = 3.3 V	+3	+1	-1	dBm
		V _{CC} = 3.6 V	3	2	0	dBm

Table 12. Second-order intermodulation distance over temperature and supply voltages*Typical values.*

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
ΔIM2	second-order intermodulation distance	f ₁ = 250 MHz; f ₂ = 251 MHz; P _{drive} = -38 dBm				
		V _{CC} = 3.0 V	43	47	51	dBc
		V _{CC} = 3.3 V	50	55	58	dBc
		V _{CC} = 3.6 V	58	62	57	dBc
		f ₁ = 950 MHz; f ₂ = 951 MHz; P _{drive} = -38 dBm				
		V _{CC} = 3.0 V	41	44	49	dBc
		V _{CC} = 3.3 V	49	53	60	dBc
		V _{CC} = 3.6 V	58	64	56	dBc

Table 13. Output third-order intercept point over temperature and supply voltages
Typical values.

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
IP _{3O}	output third-order intercept point	f ₁ = 250 MHz; f ₂ = 251 MHz; P _{drive} = -38 dBm				
		V _{CC} = 3.0 V	18	20	18	dBm
		V _{CC} = 3.3 V	20	20	19	dBm
		V _{CC} = 3.6 V	23	21	20	dBm
		f ₁ = 950 MHz; f ₂ = 951 MHz; P _{drive} = -38 dBm				
		V _{CC} = 3.0 V	18	16	14	dBm
		V _{CC} = 3.3 V	18.5	17.5	15.5	dBm
		V _{CC} = 3.6 V	20	19	17	dBm
		f ₁ = 2150 MHz; f ₂ = 2151 MHz; P _{drive} = -38 dBm				
		V _{CC} = 3.0 V	12	10	8	dBm
		V _{CC} = 3.3 V	11.5	10.5	7.5	dBm
		V _{CC} = 3.6 V	13	11	8	dBm

Table 14. -3 dB bandwidth over temperature and supply voltages
Typical values.

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
B _{-3dB}	-3 dB bandwidth	V _{CC} = 3.0 V	2.985	2.917	2.812	GHz
		V _{CC} = 3.3 V	3.062	2.965	2.857	GHz
		V _{CC} = 3.6 V	3.119	2.994	2.875	GHz

9. Test information

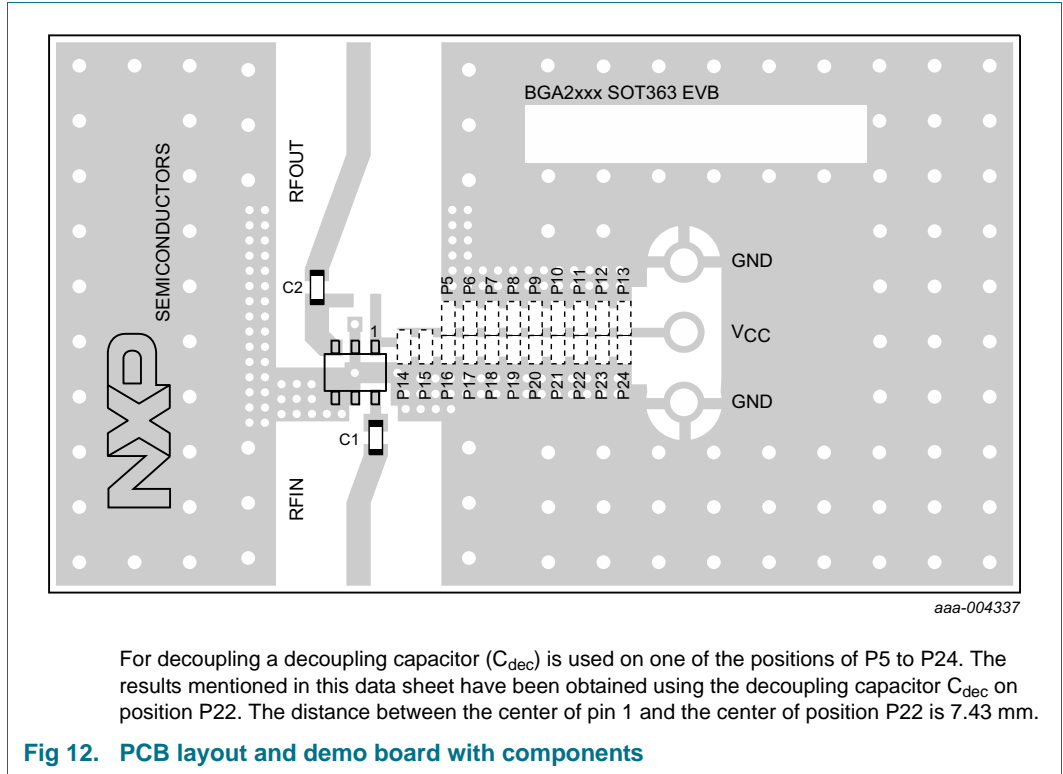


Table 15. List of components used for the typical application

Component	Description	Value	Dimensions	Remarks
C1, C2	multilayer ceramic chip capacitor	470 pF	0603	X7R RF coupling capacitor
P5 to P24 [1]	position for multilayer ceramic chip capacitor C_{dec}	470 pF	0603	X7R RF decoupling capacitor
IC1	BGA2815 MMIC	-	SOT363	

[1] For decoupling a decoupling capacitor (C_{dec}) is used on one of the positions of P5 to P24. The results mentioned in this data sheet have been obtained using the decoupling capacitor C_{dec} on position P22.

10. Package outline

Plastic surface-mounted package; 6 leads

SOT363

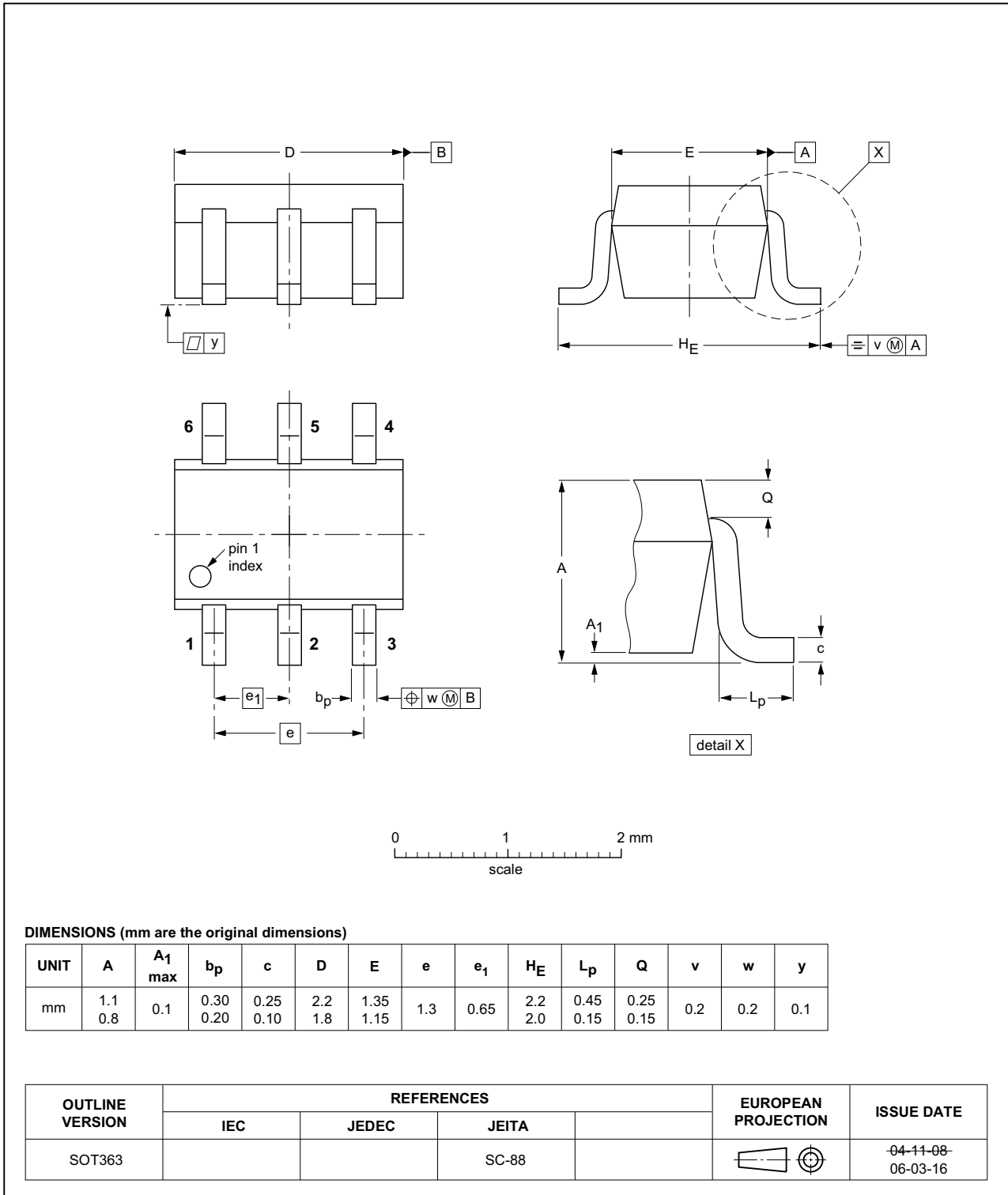


Fig 13. Package outline SOT363

11. Abbreviations

Table 16. Abbreviations

Acronym	Description
IF	Intermediate Frequency
LNA	Low-Noise Amplifier
LNB	Low-Noise Block converter
PCB	Printed-Circuit Board

12. Revision history

Table 17. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGA2815 v.5	20150529	Product data sheet	-	BGA2815 v.4
Modifications	<ul style="list-style-type: none"> Table 4 on page 2: the maximum value for P_{drive} has been changed to 10 dBm 			
BGA2815 v.4	20141209	Product data sheet	-	BGA2815 v.3
BGA2815 v.3	20130905	Product data sheet	-	BGA2815 v.2
BGA2815 v.2	20101019	Product data sheet	-	BGA2815 v.1
BGA2815 v.1	20100625	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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